

P-Channel Enhancement Mode Power MOSFET

Description

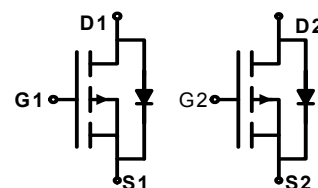
The PT111 Huses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

- $V_{DS} = -20V, I_D = -9A$
- $R_{DS(ON)} < 28m\Omega @ V_{GS} = -4.5V$
- $R_{DS(ON)} < 40m\Omega @ V_{GS} = -2.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

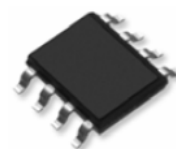
- Motor drive
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOP-8 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
PT111H	PT111H	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-9	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-40	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	42	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=-250\mu A$	-20	-	-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.5	-0.7	-1.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-6A	-	22	28	mΩ
		V _{GS} =-2.5V, I _D =-5A		32	40	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-15V, I _D =-6A	-	17	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V, F=1.0MHz	-	2100	-	PF
Output Capacitance	C _{oss}		-	498	-	PF
Reverse Transfer Capacitance	C _{rss}		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, R _L =10Ω, V _{GS} =-4.5V, R _{GEN} =6Ω	-	25	-	nS
Turn-on Rise Time	t _r		-	30	-	nS
Turn-Off Delay Time	t _{d(off)}		-	70	-	nS
Turn-Off Fall Time	t _f		-	50	-	nS
Total Gate Charge	Q _g	V _{DS} =-10V, I _D =-6A, V _{GS} =-4.5V	-	17	-	nC
Gate-Source Charge	Q _{gs}		-	4.1	-	nC
Gate-Drain Charge	Q _{gd}		-	4.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-9A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

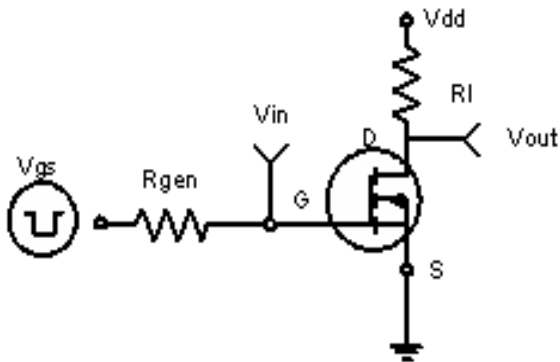


Figure 1 Switching Test Circuit

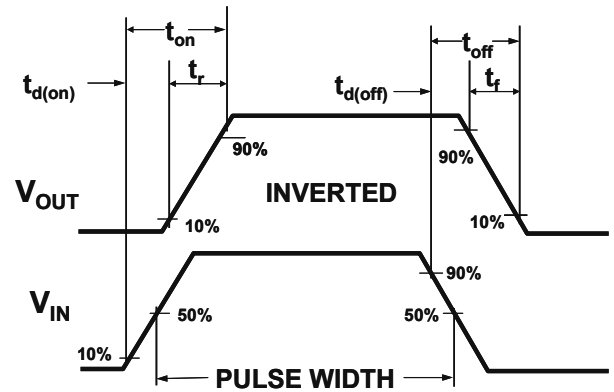


Figure 2 Switching Waveforms

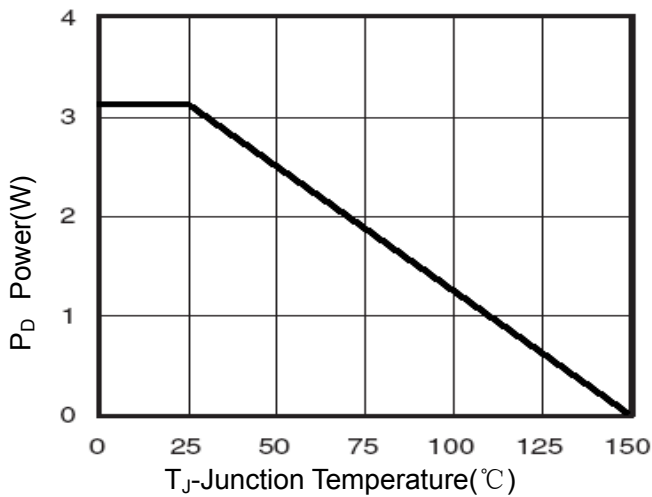


Figure 3 Power Dissipation

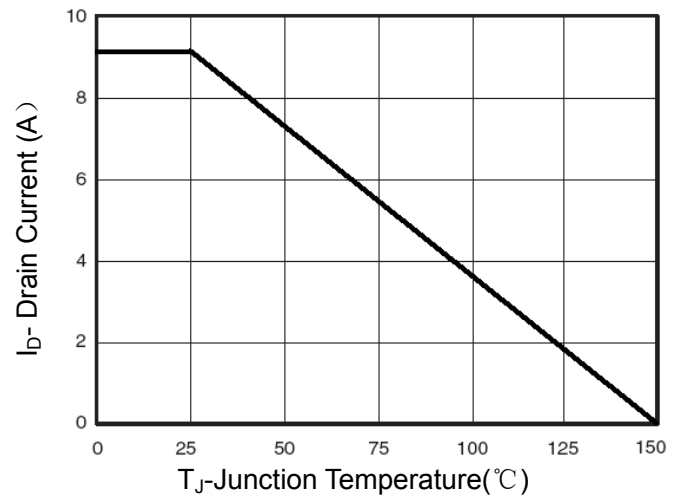


Figure 4 Drain Current

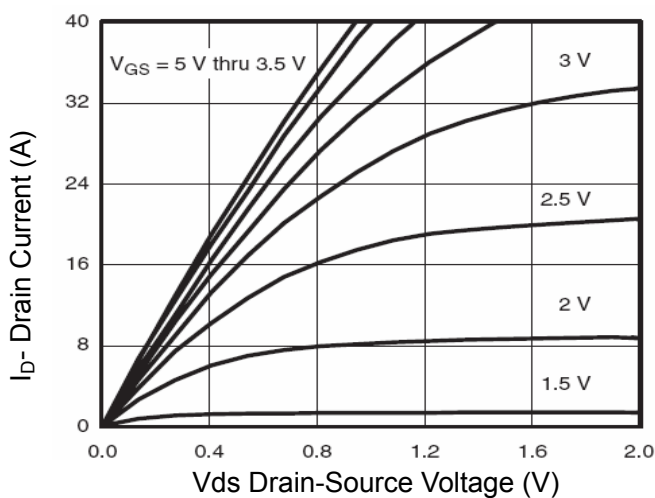


Figure 5 Output Characteristics

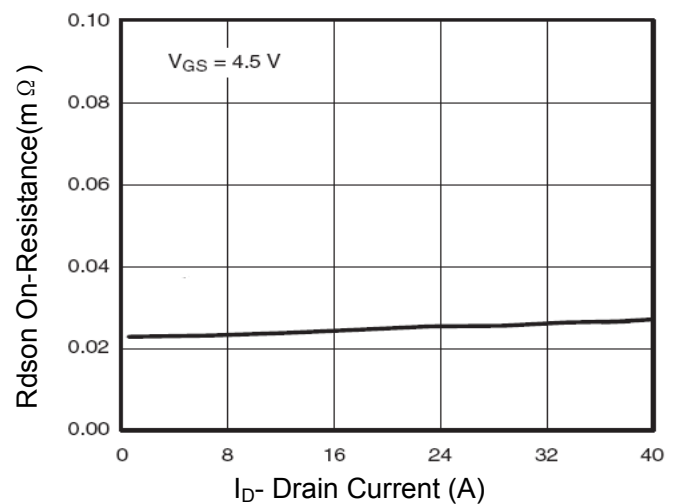


Figure 6 Drain-Source On-Resistance

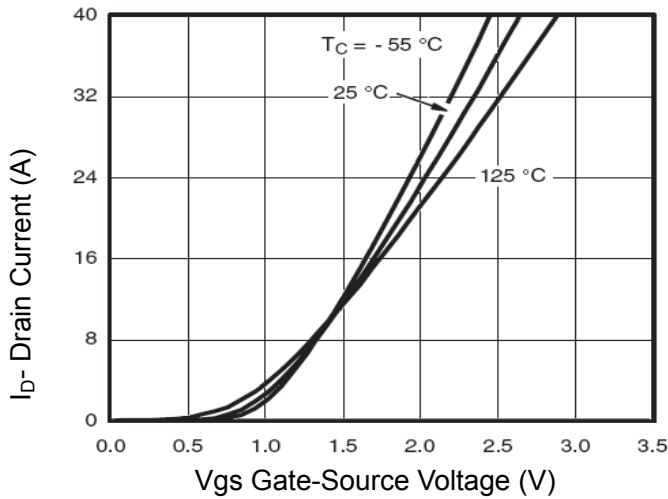


Figure 7 Transfer Characteristics

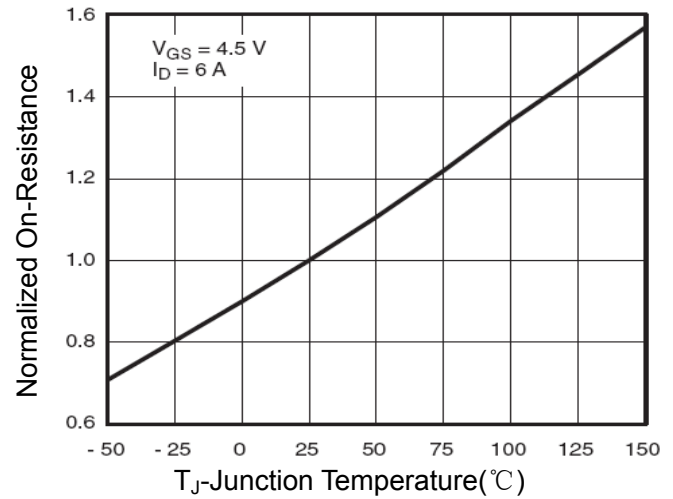


Figure 8 Drain-Source On-Resistance

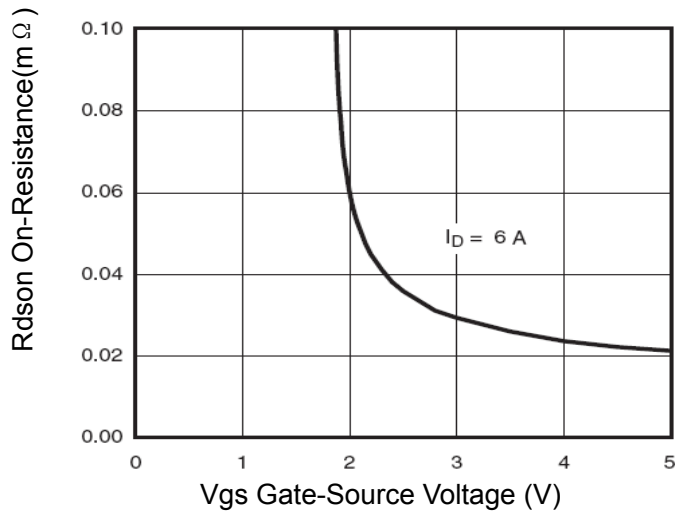


Figure 9 Rdson vs Vgs

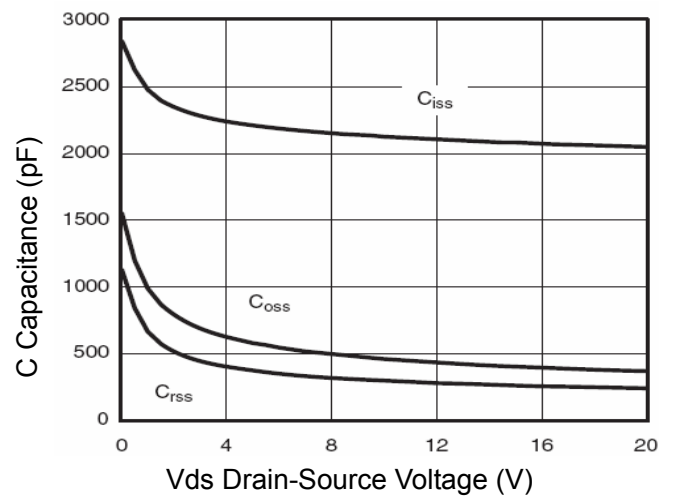


Figure 10 Capacitance vs Vds

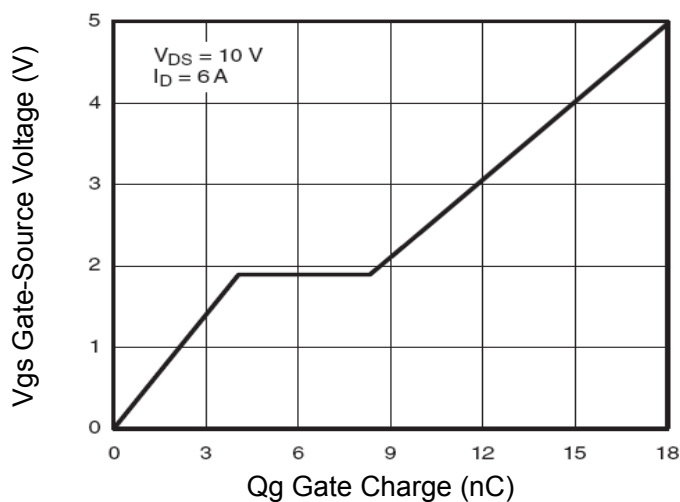


Figure 11 Gate Charge

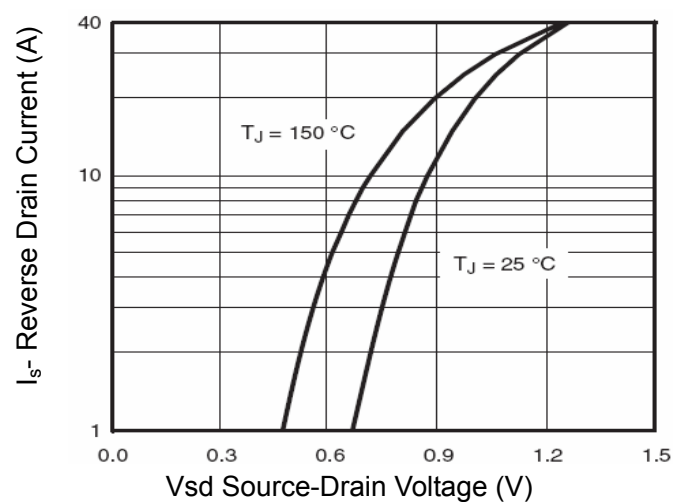


Figure 12 Source- Drain Diode Forward

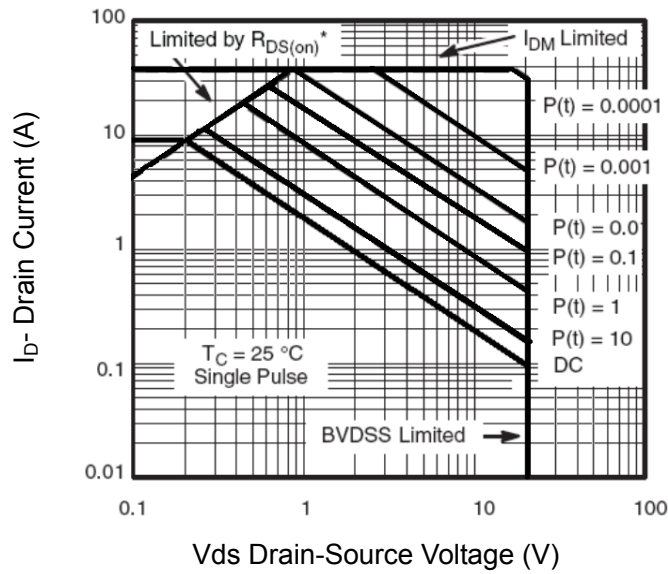


Figure 13 Safe Operation Area

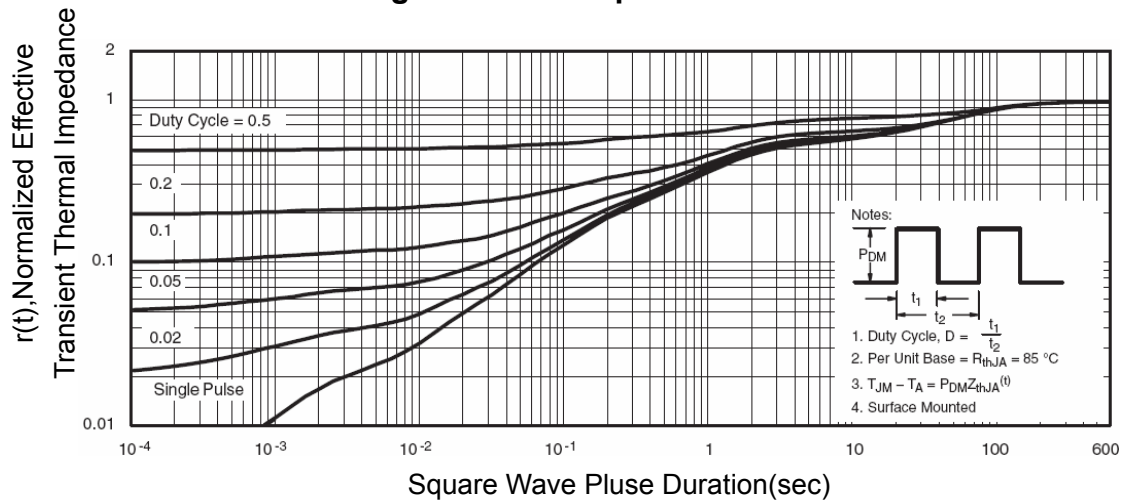
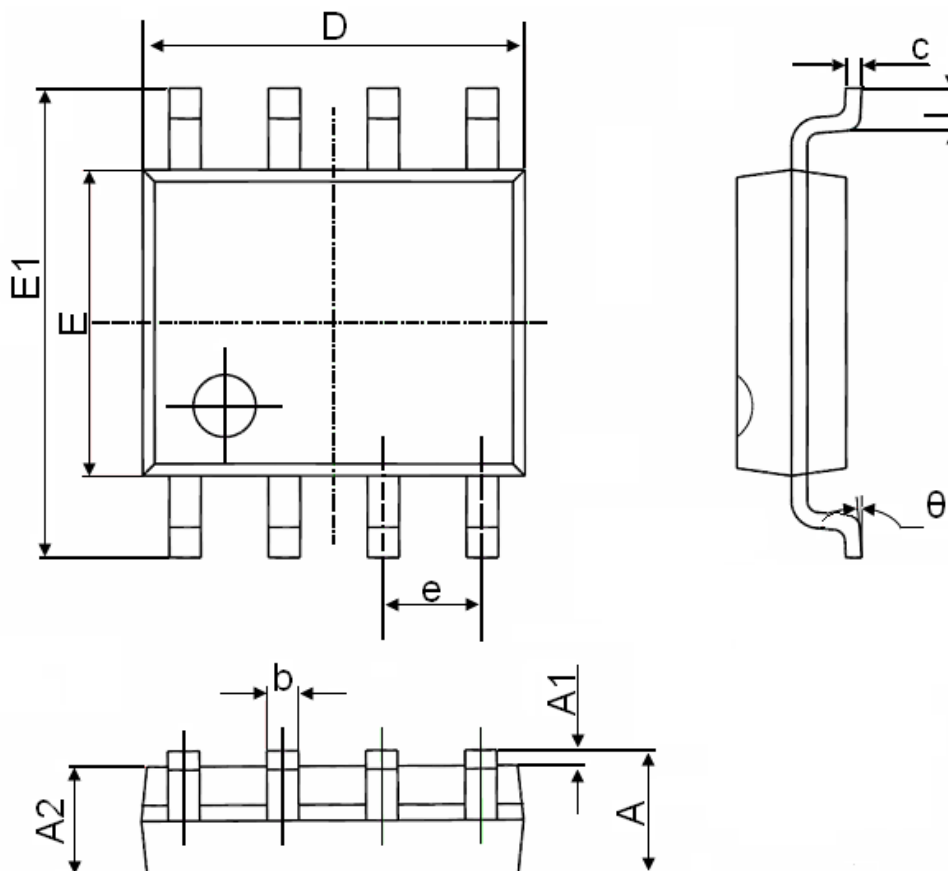


Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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